Schmitt-Trigger Inverter

The MC74VHC1G14 is a single gate CMOS Schmitt-trigger inverter fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1G14 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1G14 to be used to interface 5V circuits to 3V circuits.

The MC74VHC1G14 can be used to enhance noise immunity or to square up slowly changing waveforms.

- High Speed: $t_{PD} = 4.0$ ns (Typ) at $V_{CC} = 5V$
- Low Power Dissipation: $I_{CC} = 2\mu A$ (Max) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA

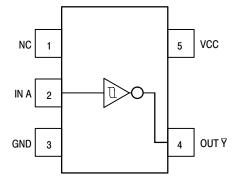
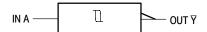
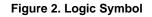


Figure 1. 5-Lead SOT-353 Pinout (Top View)







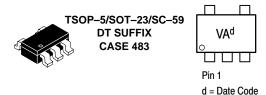
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MARKING DIAGRAMS



d = Date Code



	PIN ASSIGNMENT						
1	NC						
2	IN A						
3	GND						
4	OUT Y						
5	VCC						

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

FUNCTION TABLE

A Input	Y Output
L	н
Н	L

Semiconductor Components Industries, LLC, 2000 August, 2000 – Rev. 4

MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V _{CC}	-0.5 to +7.0	V
DC Input Voltage	V _{IN}	-0.5 to +7.0	V
DC Output Voltage V _{CC} = 0 High or Low State	V _{OUT}	−0.5 to 7.0 −0.5 to V _{CC} + 0.5	V
Input Diode Current	I _{IK}	-20	mA
Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$	I _{OK}	+20	mA
DC Output Current, per Pin	I _{OUT}	+25	mA
DC Supply Current, V _{CC} and GND	I _{CC}	+50	mA
Power dissipation in still air, SC-88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T _{stg}	-65 to +150	°C

* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC-88A Package: -3 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	V _{CC}	2.0	5.5	V
DC Input Voltage	V _{IN}	0.0	5.5	V
DC Output Voltage	V _{OUT}	0.0	V _{CC}	V
Operating Temperature Range	T _A	-55	+125	°C

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

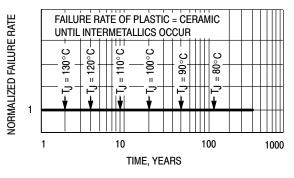


Figure 3. Failure Rate vs. Time Junction Temperature

			Vcc	ר	Γ _A = 25°0	C	TA ≤	85°C	T _A ≤ ′	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Мах	Unit
V _{T+}	Positive Threshold Voltage		3.0 4.5 5.5	1.85 2.86 3.50	2.0 3.0 3.6	2.20 3.15 3.85		2.20 3.15 3.85		2.20 3.15 3.85	V
V _{T-}	Negative Threshold Voltage		3.0 4.5 5.5	0.9 1.35 1.65	1.5 2.3 2.9	1.65 2.46 3.05	0.9 1.35 1.65		0.9 1.35 1.65		V
V _H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.57 0.67 0.74	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	V
V _{OH}	Minimum High–Level Output Voltage I _{OH} = –50µA	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		I _{OH} = -4mA I _{OH} = -8mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		I _{OL} = 4mA I _{OL} = 8mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	V_{IN} = 5.5V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μA

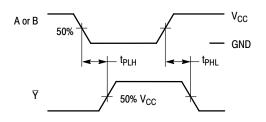
DC ELECTRICAL CHARACTERISTICS

AC ELECTRICAL CHARACTERISTICS (C_{load} = 50 pF, Input t_r/t_f = 3.0ns)

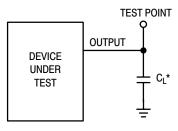
					Γ _A = 25°0	2	T _A ≤ 85°C		T _A ≤ 125°C		
Symbol	Parameter	Test Cond	itions	Min	Тур	Max	Min	Max	Min	Мах	Unit
t _{PLH} , t _{PHL}	Maximum Propogation Delay,	$V_{CC} = 3.3 \pm 0.3 V$	C _L = 15 pF C _L = 50 pF		7.0 8.5	12.8 16.3	1.0 1.0	15.0 18.5	1.0 1.0	17.0 20.5	ns
	A to Y	$V_{CC} = 5.0 \pm 0.5 V$	C _L = 15 pF C _L = 50 pF		4.0 5.5	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	11.5 13.5	
C _{IN}	Maximum Input Capacitance				5	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0V		ĺ
C _{PD}	Power Dissipation Capacitance (Note 1.)	7.0	pF	
				•

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.





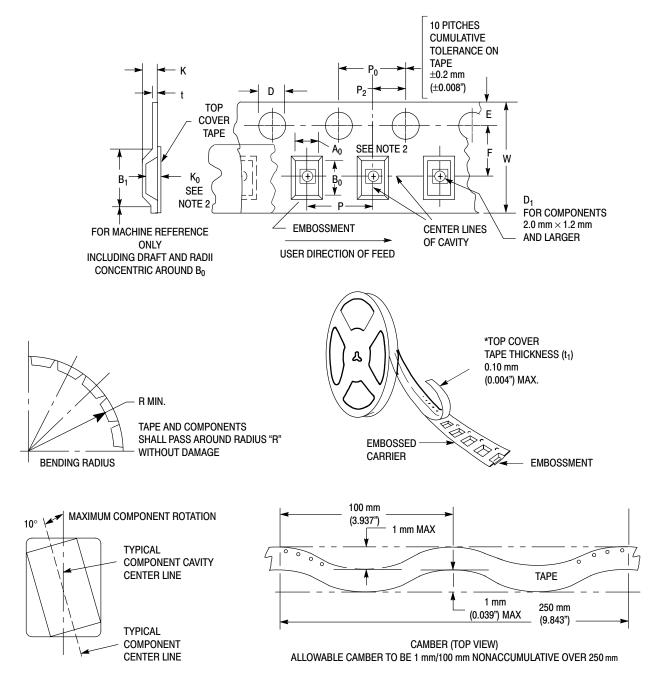


*Includes all probe and jig capacitance

Figure 5. Test Circuit

DEVICE ORDERING INFORMATION

			Device Nome	nclature				
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Tape and Reel Size
MC74VHC1G14DFT2	MC	74	VHC1G	14	DF	T2	SC-88A/ SOT-353 /SC-70	178mm (7") 3000 Unit
MC74VHC1G14DFT4	MC	74	VHC1G	14	DF	T4	SC-88A/ SOT-353 /SC-70	330mm (13") 100000 Unit
MC74VHC1G14DTT1	MC	74	VHC1G	14	DT	T1	TSOP5/ SOT-23 /SC-59	178mm (7") 3000 Unit
MC74VHC1G14DTT3	MC	74	VHC1G	14	DT	Т3	TSOP5/ SOT–23 /SC–59	330mm (13") 100000 Unit





Tape Size	B ₁ Max	D	D ₁	Е	F	к	Р	P ₀	P ₂	R	т	w
8 mm	4.35 mm (0.171")	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

EMBOSSED	CARRIER	DIMENSIONS	(See Note	s 1	and 2)
LINDOOOLD	OANNEN	DIMILINGIONO		5 1	

1. Metric Dimensions Govern-English are in parentheses for reference only.

2. A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

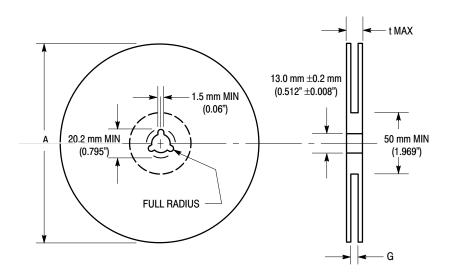
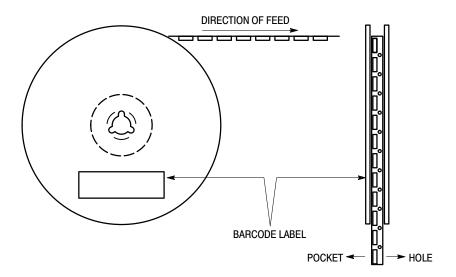


Figure 7. Reel Dimensions

REEL DIMENSIONS

Tape Size	T&R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")
8 mm	T3, T4	330 mm (13")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")





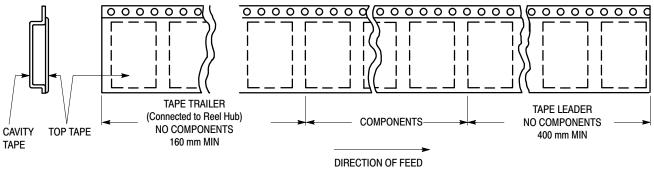


Figure 9. Tape Ends for Finished Goods

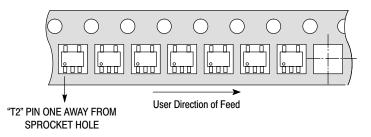


Figure 10. DFT2 and DFT4 (SC88A) Reel Configuration/Orientation

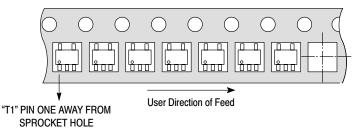
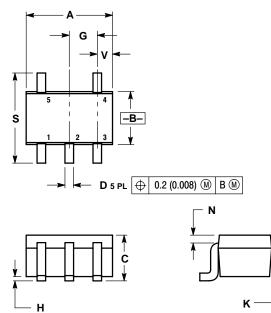


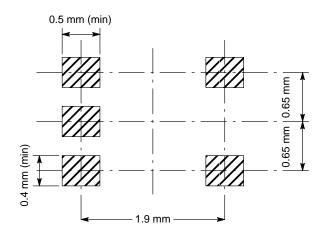
Figure 11. DTT1 and DTT3 (TSOP5) Reel Configuration/Orientation

PACKAGE DIMENSIONS

SC-88A / SOT-353 / SC-70 DF SUFFIX 5-LEAD PACKAGE CASE 419A-01 ISSUE B



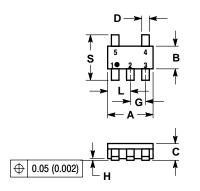
DIMEN Y14.5	isioning M, 1982. Rolling			NG PER A	N
	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	1
В	0.045	0.053	1.15	1.35	
C	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026 BSC		0.65 BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
Ν	0.008 REF		0.20 REF		
S	0.079	0.087	2.00	2.20	
۷	0.012	0.016	0.30	0.40	1



PACKAGE DIMENSIONS

TSOP-5 / SOT-23 / SC-59 DT SUFFIX 5-LEAD PACKAGE CASE 483-01 ISSUE A

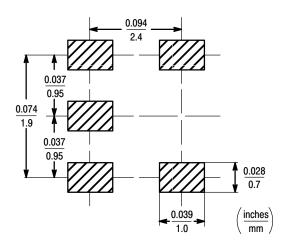
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NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
С	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.00	0.0335	0.0413
Η	0.013	0.100	0.0005	0.0040
ſ	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
М	0 °	10 °	0°	10 °
S	2.50	3.00	0.0985	0.1181



<u>Notes</u>

<u>Notes</u>

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